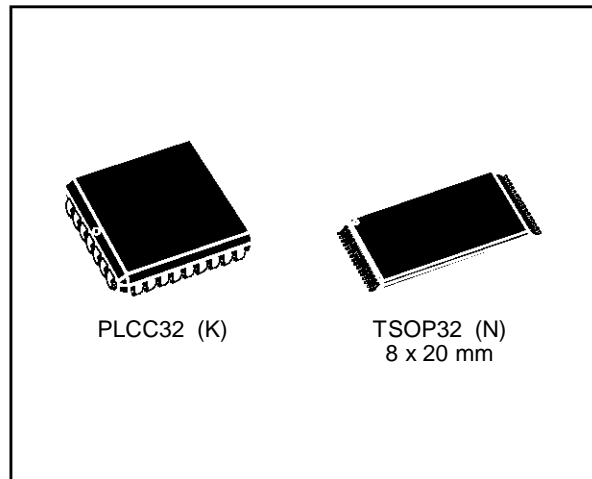


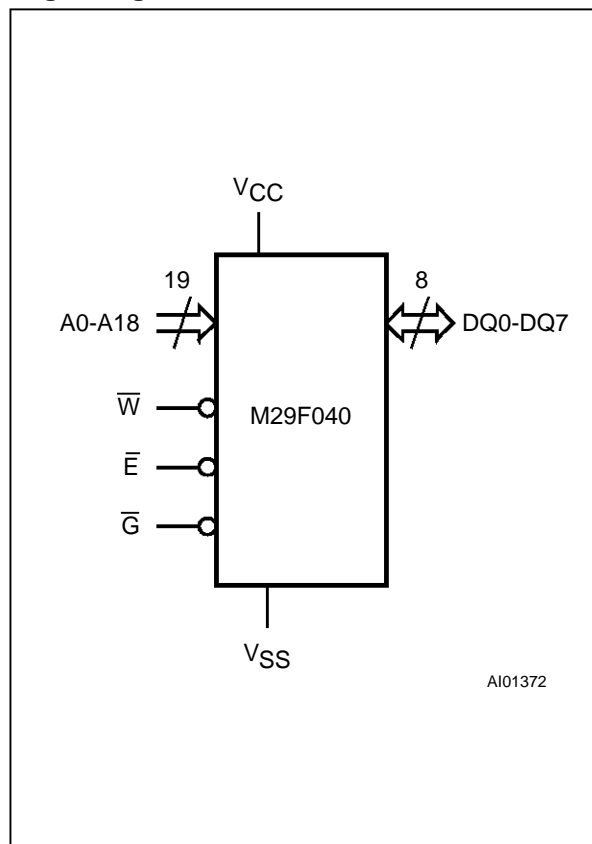
## SINGLE SUPPLY 4 Megabit (512K x 8, Sector Erase) FLASH MEMORY

### DATA BRIEFING

- FAST ACCESS TIME: 70ns
- 5V ± 10% SUPPLY VOLTAGE for PROGRAM and ERASE OPERATIONS
- 5V ± 10% SUPPLY VOLTAGE in READ OPERATIONS
- BYTE PROGRAMMING TIME: 10µs typical
- ERASE TIME
  - Sector: 1.0 sec typical
  - Bulk: 2.5 sec typical
- PROGRAM/ERASE CONTROLLER (P/E.C.)
  - Program Byte-by-Byte
  - Data Polling and Toggle Protocol for P/E.C. Status
- MEMORY ERASE in SECTORS
  - 8 Sectors of 64K Bytes each
  - Sector Protection
  - Multisector Erase
- ERASE SUSPEND and RESUME MODES
- 100,000 PROGRAM/ERASE CYCLES per SECTOR
- LOW POWER CONSUMPTION
  - 25µA typical current in Standby
  - 8mA typical current for Read
  - Automatic CMOS Standby Mode



### Logic Diagram

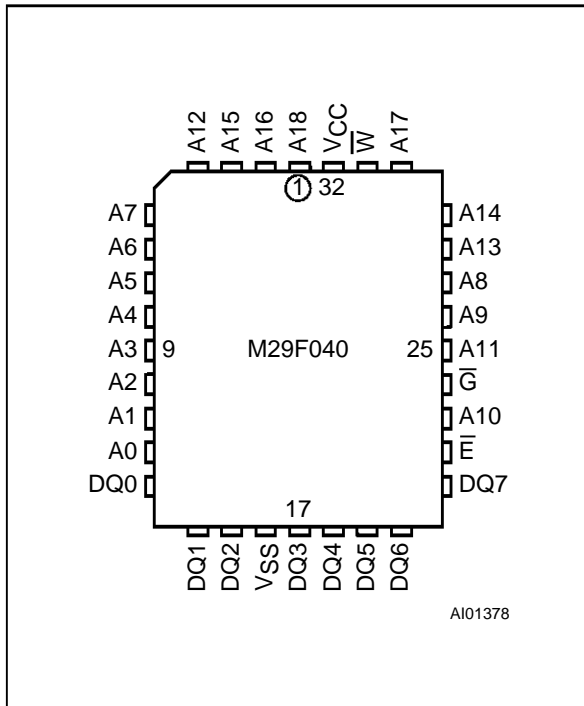


### DESCRIPTION

The M29F040 is a non-volatile memory that may be erased electrically at the sector level, and programmed Byte-by-Byte.

The interface is directly compatible with most microprocessors. PLCC32 and TSOP32 (8 x 20mm) packages are available. Reverse pin out is available for the TSOP package upon request.

LCC Pin Connections



Signal Names

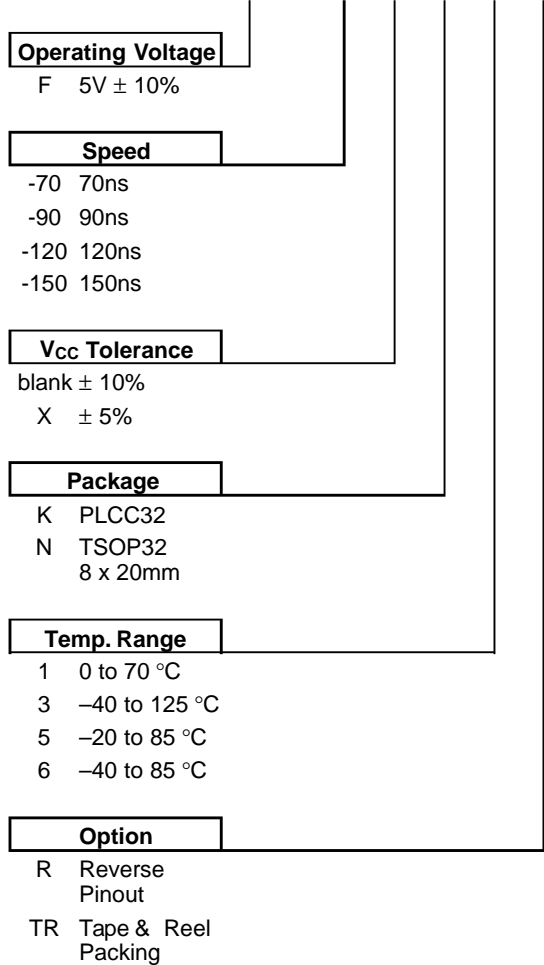
A0-A18	Address Inputs
DQ0-DQ7	Data Input / Outputs
$\bar{E}$	Chip Enable
$\bar{G}$	Output Enable
$\bar{W}$	Write Enable
Vcc	Supply Voltage
Vss	Ground

Ordering Information Scheme

For a list of available options refer to the current Memory Shortform catalogue.

For further information on any aspect of this device, please contact the SGS-THOMSON Sales Office nearest to you.

Example: M29F040 -70 X N 1 TR



TSOP Pin Connections

